

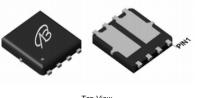
NVMFD027N10MCL-VB Datasheet Dual N-Channel 100V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a		
100	0.018at V _{GS} = 10 V	35		
	0.022at V _{GS} = 4.5 V	36		

FEATURES

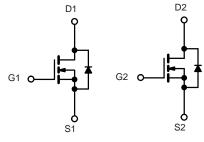
- 175 °C Junction Temperature
- Trench technology Power MOSFET
- Material categorization:





DFN5X6

Top View



N-Channel MOSFET N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V _{GS}	±20	V			
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	1-	35			
	T _C = 100 °C	I _D	20 ^a			
Pulsed Drain Current	I _{DM}	105	А			
Continuous Source Current (Diode Conduction)	۱ _S	76 ^a				
Avalanche Current	I _{AS}	82				
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	110	mJ		
Maximum Dowar Dissinction	T _C = 25 °C	P	136	w		
Maximum Power Dissipation	T _A = 25 °C	P _D	3 ^b , 8.3 ^{b, c}			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maujanum lumation to Ambienta	$t \le 10 \text{ sec}$	R _{thJA}	15	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State		60	50	
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t \leq 10 s.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static				.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100		V		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	2	3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		$V_{DS} = 30V, V_{GS} = 0 V$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0 V, T _J = 125 °C			50	μA	
		V _{DS} = 30V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			А	
		V _{GS} = 10 V, I _D = 20 A		0.018			
Drain-Source On-State Resistance ^b	P	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.008		0	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.010		Ω	
		V _{GS} = 4.5 V, I _D = 12A		0.022			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic							
Input Capacitance	C _{iss}			3900			
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz		470		pF	
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Qg			89	70		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		26		nC	
Gate-Drain Charge ^c	Q _{gd}			23			
Turn-On Delay Time ^c	t _{d(on)}			21	25		
Rise Time ^c	t _r	V_{DD} = 100 V, R _L = 0.6 Ω		15	25	20	
Turn-Off Delay Time ^c	t _{d(off)}	$\text{I}_\text{D}\cong$ 50 A, V_GEN = 10 V, R_g = 2.5 Ω		35	50	ns	
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				105	А	
Diode Forward Voltage	V_{SD}	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/µs		4	135	ns	

SPECIFICATIONS (T₁ = 25 °C, unless otherwise noted)

Notes:

a. For design aid only; not subject to production testing.

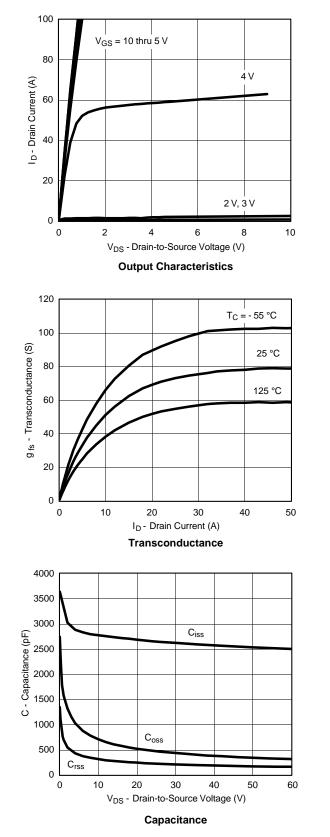
b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

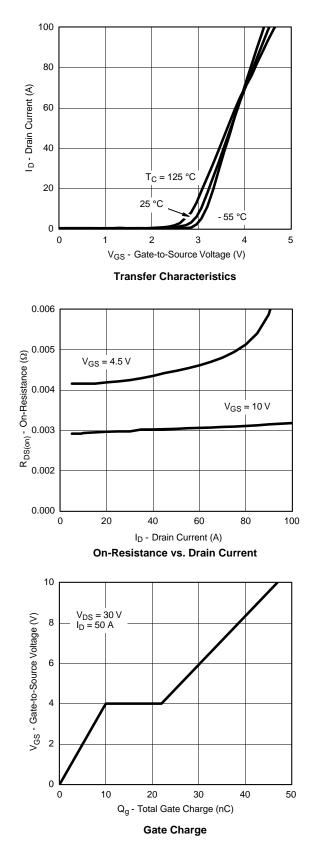
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



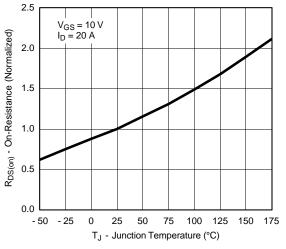
TYPICAL CHARACTERISTICS (25 °C unless noted)



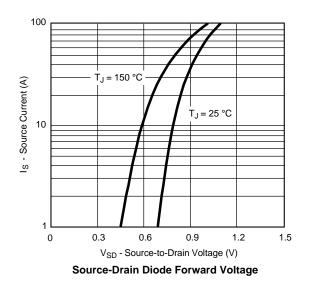




TYPICAL CHARACTERISTICS (25 °C unless noted)



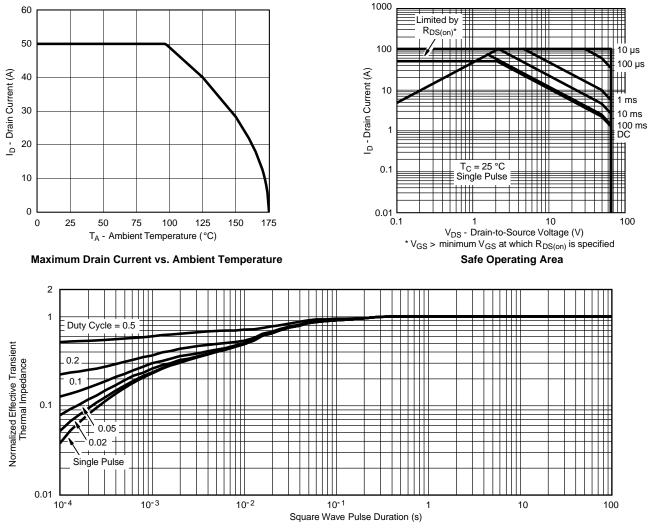
On-Resistance vs. Junction Temperature



NVMFD027N10MCL-VB



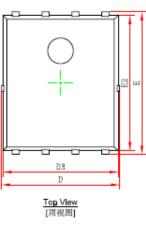
THERMAL RATINGS

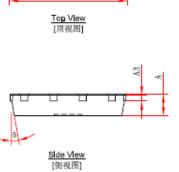


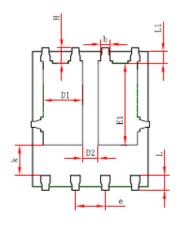
Normalized Thermal Transient Impedance, Junction-to-Case



PDFNWB5×6-8L-A PACKAGE OUTLINE DIMENSIONS







<u>Bottom Vlew</u> [背视图]

Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.900	1.000	0.035	0.039	
A3	0.254	0.254 REF. 0.010RE		REF.	
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	1.470	1.870	0.058	0.074	
D2	0.470	0.870	0.019	0.034	
E1	3.375	3.575	0.133	0.141	
D3	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
e	1.270TYP.		0.050	DTYP.	
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	10°	12°	10°	12°	



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